N-Ch 40V Fast Switching MOSFETs

Features

- Split Gate Trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

Product Summary

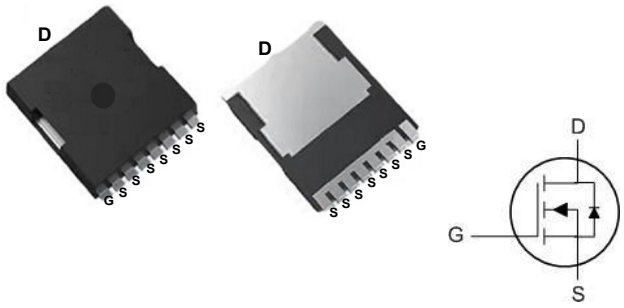
Green

BVDSS	RDSON	ID
40V	0.75mΩ	320A

Applications

- DC-DC Converters
- Power management functions
- Synchronous-rectification applications

TOLL-8L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1,6]	320	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1,6]	160	A
I_{DM}	Pulsed Drain Current[2]	720	A
EAS	Single Pulse Avalanche Energy[3]	450	mJ
I_{AS}	Avalanche Current	---	A
P_D@T_C=25℃	Total Power Dissipation[4]	114	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	55	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	1.1	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	40	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	---	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=50A	---	0.75	1.1	mΩ
		V_{GS}=4.5V , I_D=25A	---	1.4	2.0	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.3	1.7	2.3	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=40V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=40V, V_{GS}=0V , T_J=100℃	---	---	100	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=10V , I_D=20A	---	---	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	3.5	---	Ω
Q_g	Total Gate Charge	V_{DS}=20V , V_{GS}=10V , I_D=50A	---	87	---	nC
Q_{gs}	Gate-Source Charge		---	18	---	
Q_{gd}	Gate-Drain Charge		---	15	---	
$T_{d(on)}$	Turn-On Delay Time	VGS=10V, VDD=20V, RG=3Ω, ID=50A	---	14	---	ns
T_r	Rise Time		---	15	---	
$T_{d(off)}$	Turn-Off Delay Time		---	84	---	
T_f	Fall Time		---	44	---	
C_{iss}	Input Capacitance	V_{DS}=20V , V_{GS}=0V , f=1MHz	---	5500	---	pF
C_{oss}	Output Capacitance		---	1850	---	
C_{rss}	Reverse Transfer Capacitance		---	65	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	320	A
I_{SM}	Pulsed Source Current[2,4]		---	---	720	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	1.2	V
t_{rr}	Reverse Recovery Time	IF=50A , di/dt=100A/μs , T_J=25℃	---	55	---	nS
Q_{rr}	Reverse Recovery Charge		---	53	---	nC

Note :

1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3.The EAS data shows Max. rating . The test condition is TJ = 25ÁC,VDD=25V, VGS=10V, L=0.5mH,

4.The power dissipation is limited by 150℃ junction temperature

5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Electrical and Thermal Characteristics Diagramstics

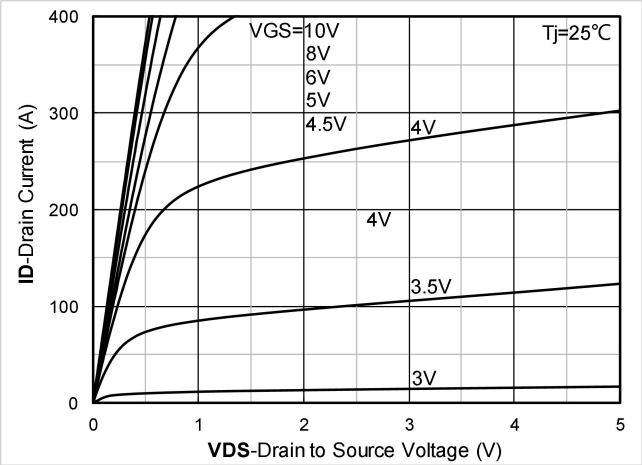


Figure 1. Output Characteristics

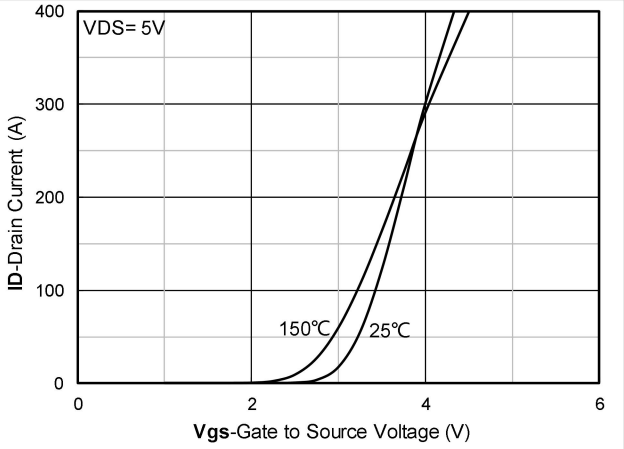


Figure 2. Transfer Characteristics

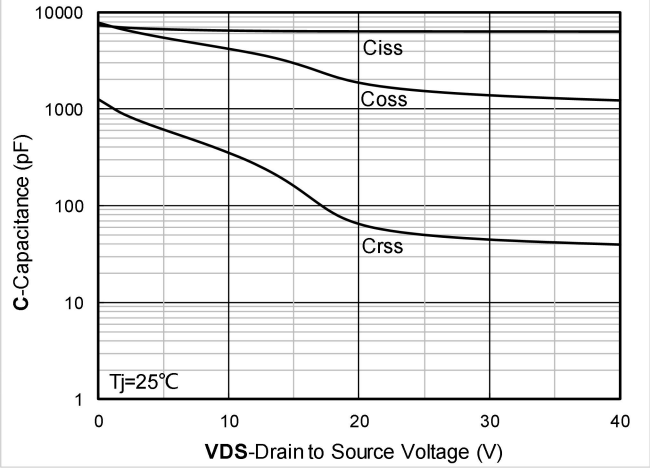


Figure 3. Capacitance Characteristics

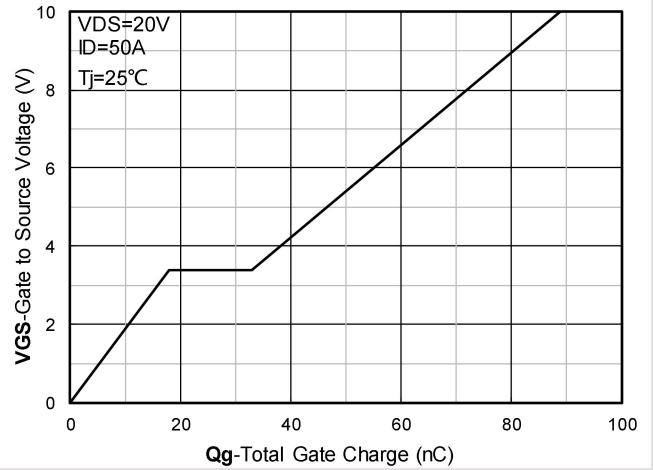


Figure 4. Gate Charge

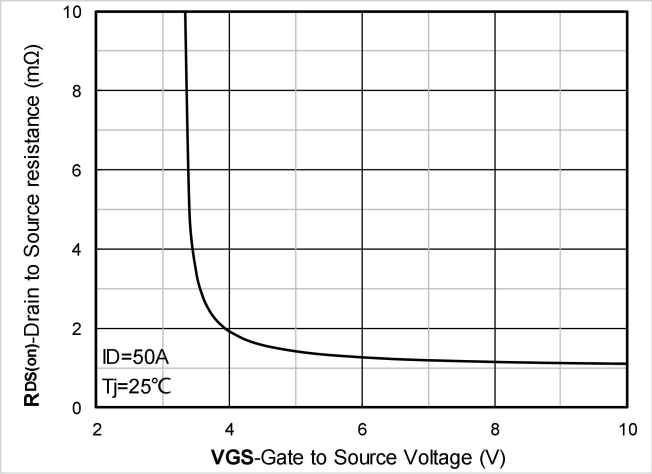


Figure 5. On-Resistance vs Gate to Source Voltage

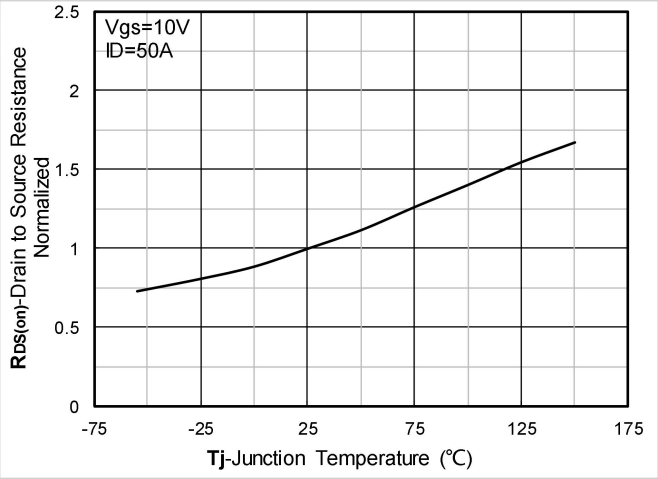


Figure 6. Normalized On-Resistance

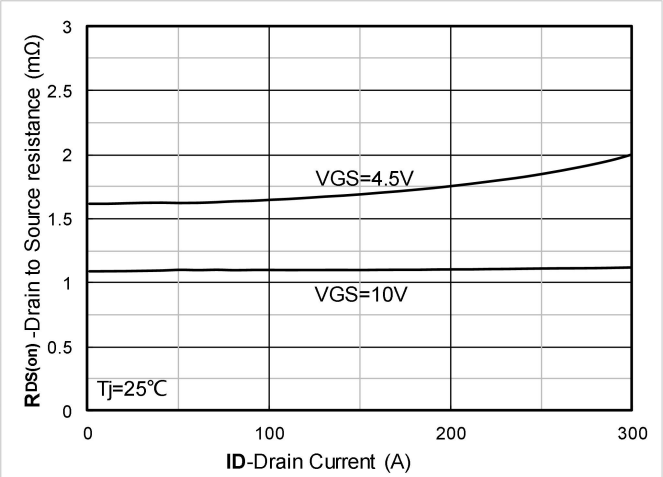


Figure 7. $R_{DS(on)}$ VS Drain Current

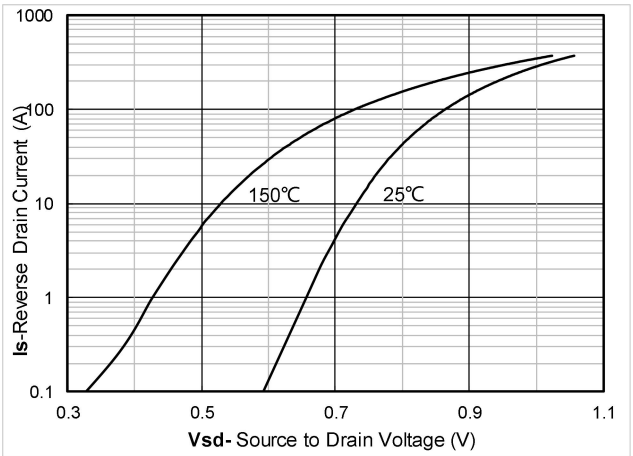


Figure 8. Forward characteristics of reverse diode

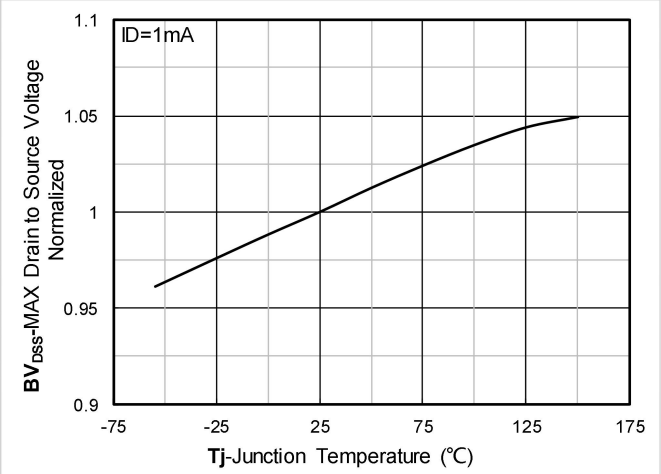


Figure 9. Normalized breakdown voltage

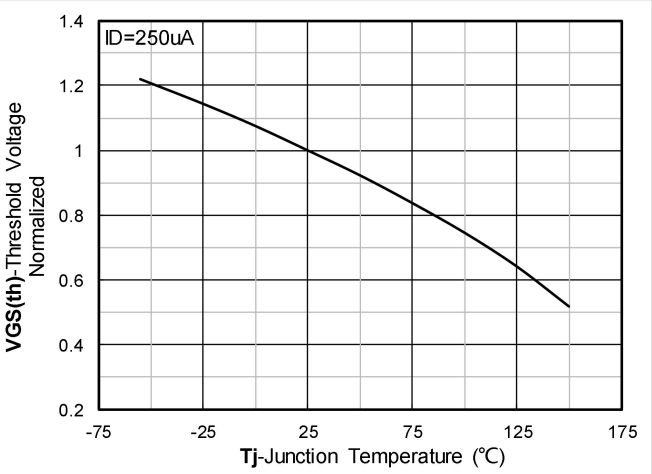


Figure 10. Normalized Threshold voltage

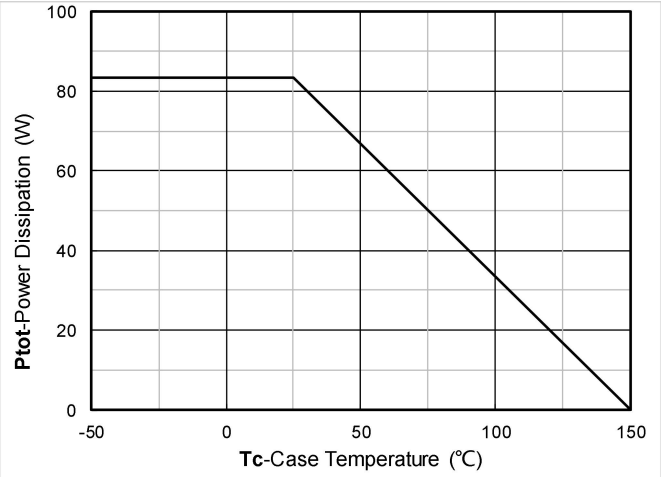


Figure 11. Power dissipation

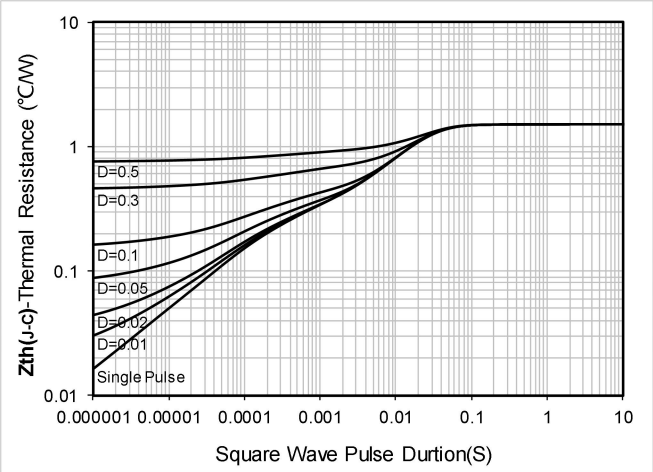


Figure 12. Maximum Transient Thermal Impedance

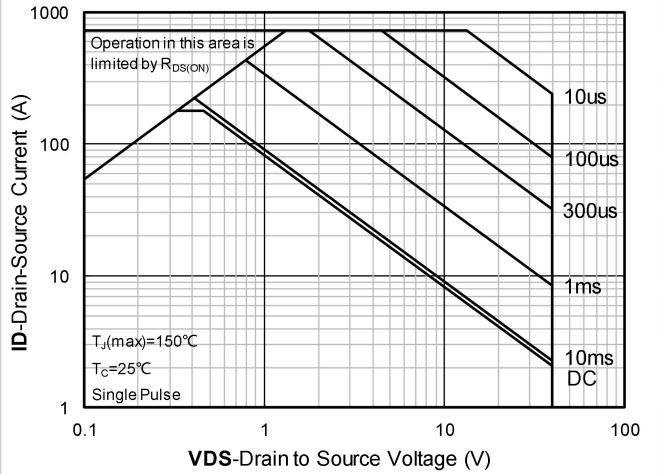
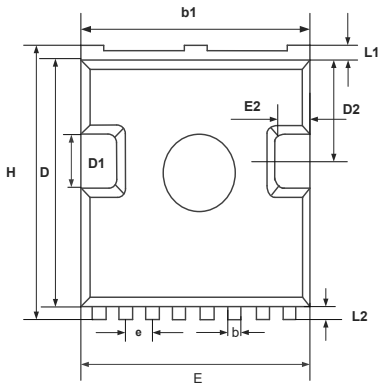
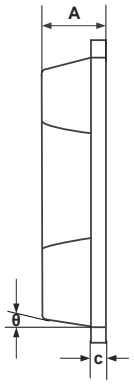


Figure 13. Safe Operation Area

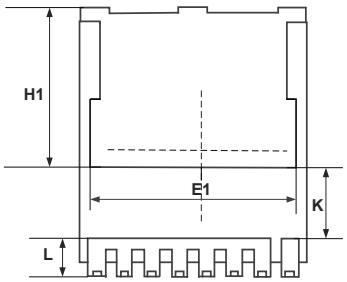
Mechanical Dimensions for TOLL-8L



TOP VIEW



SIDE VIEW



BOTTTOM VIEW

COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	2.20	2.40
b	0.60	0.90
b1	9.70	9.90
c	0.40	0.60
D	10.20	10.60
D1	3.10	3.50
D2	4.45	4.75
E	9.70	10.10
E1	7.80BSC	
E2	0.50	0.70
e	1.200 BSC	
H	11.45	11.90
H1	6.75 BSC	
K	3.10 REF	
L	1.70	2.10
L1	0.60	0.80
L2	0.50	0.70
θ	10° REF	